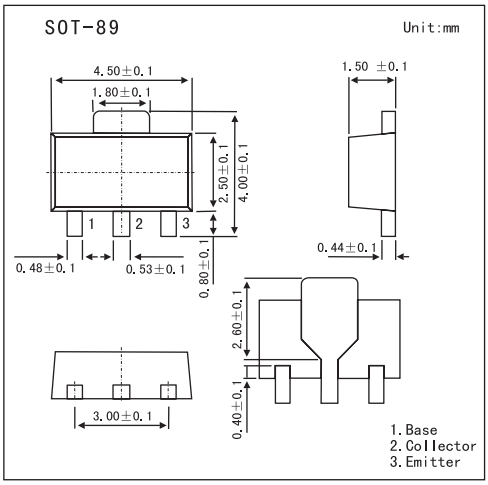
Silicon PNP Epitaxial Planar Type

2SB1440



■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-50	V
Emitter-base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-3	A
Collector current	I_C	-2	A
Collector power dissipation	P_C	1	W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = -10 μA, I_E = 0	-50			V
Collector-emitter voltage	V_{CEO}	I_C = -1 mA, I_B = 0	-50			V
Emitter-base voltage	V_{EBO}	I_E = -10 μA, I_C = 0	-5			V
Forward current transfer ratio	h_{FE}	V_{CE} = -2 V, I_C = -200 mA	120		340	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = -1 A, I_B = - 50 mA		-0.2	-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = -1 A, I_B = - 50 mA		-0.85	-1.2	
Transition frequency	f_T	V_{CB} = -10 V, I_E = 50 mA, f = 200 MHz		80		MHz
Collector output capacitance	C_{ob}	V_{CB} = -10 V, I_E = 0, f = 1 MHz		45	60	pF

■ h_{FE} Classification

Marking	1I	
Rank	R	S
h_{FE}	120～240	170～340